

FORM PTO-1449
(REV.7-80)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

500466.03

APPLICATION NO.

not yet assigned 10/18/94 79

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)

Kie Y Ahn and Leonard Forbes

FILING DATE

Concurrently herewith

GROUP ART UNIT

not yet assigned 2879

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
K.G.	AA	3,665,241	05/23/72	Spindt et al.	313	351	
K.G.	AB	3,755,704	08/28/73	Spindt et al.	313	309	
K.G.	AC	3,812,559	05/28/74	Spindt et al.	29	25	
K.G.	AD	3,954,523	05/04/76	Magdo et al.	438	409	
K.G.	AE	4,016,017	04/05/77	Aboaf et al.	438	441	
K.G.	AF	4,266,233	05/05/81	Bertotti et al.	257	271	
K.G.	AG	4,652,467	03/24/87	Brinker et al.	427	246	
K.G.	AH	4,857,161	08/15/89	Borel et al.	445	24	
K.G.	AI	4,987,101	01/22/91	Kaanta et al.	438	619	
K.G.	AJ	5,103,288	04/07/92	Dakamoto et al.	257	758	
K.G.	AK	5,142,184	8/25/92	Kane	313	309	
K.G.	AL	5,186,670	02/16/93	Doan et al.	445	24	
K.G.	AM	5,194,780	3/16/93	Meyer	315	169.3	
K.G.	AN	5,229,331	07/20/93	Doan et al.	437	228	
K.G.	AO	5,259,799	11/09/93	Doan et al.	445	24	
K.G.	AP	5,358,908	10/25/94	Reinbert et al.	438	20	
K.G.	AQ	5,372,973	12/13/94	Doan et al.	437	228	
K.G.	AR	5,430,300	07/04/95	Yue et al.	445	50	
K.G.	AS	5,458,518	10/17/95	Lee	445	24	
K.G.	AT	5,470,801	11/28/95	Kapoor et al.	438	471	
K.G.	AU	5,473,222	12/05/95	Theony et al.	315	169.1	
K.G.	AV	5,483,067	01/09/96	Fujii et al.	250	338.3	
K.G.	AW	5,529,524	06/25/96	Jones	445	24	
K.G.	AX	5,569,058	10/29/96	Gnade et al.	445	24	

EXAMINER

Karabi Gubaray

DATE CONSIDERED

12/21/04

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FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 500466.03		APPLICATION NO. not yet assigned	
INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>				APPLICANT(S) Kie Y Ahn and Leonard Forbes			
				FILING DATE Concurrently herewith		GROUP ART UNIT 2879 not yet assigned	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
K.G	AY	5,578,896	11/26/96	Huang	313	309	
K.G	AZ	5,585,301	12/17/96	Lee et al.	437	60	
K.G	BA	5,597,444	01/28/97	Gilton	156	643	
K.G	BB	5,653,619	08/05/97	Cloud et al.	445	24	
K.G	BC	5,663,608	09/02/97	Jones et al.	313	309	
K.G	BD	5,684,356	11/04/97	Jeng et al.	445	70	
K.G	BE	5,712,534	1/27/98	Lee et al.	315	169.3	
K.G	BF	5,793,154	8/11/98	Itoh et al.	313	308	
K.G	BG	5,804,910	09/08/98	Tjaden et al.	313	310	
K.G	BH	5,853,492	12/29/98	Cathey et al.	134	3	
K.G	BI	5,869,169	02/09/99	Jones	428	213	
K.G	BJ	5,898,258	04/27/99	Sakai et al.	313	309	
K.G	BK	6,028,322	02/22/00	Moradi	257	10	
K.G	BL	6,232,705	05/15/01	Forbes et al.	313	309	
K.G	BM	6,251,470	06/26/01	Forbes et al.	427	97	
K.G	BN	6,255,156	07/03/01	Forbes et al.	438	235	
K.G	BO	6,277,765 B1	08/21/01	Cheng et al.	438	773	
K.G	BP	6,333,215 B1	12/25/01	Matsuda et al.	438	149	

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	BQ						

OTHER PRIOR ART <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
K.G	BR	Anderson, R.C. et al., "Porous Polycrystalline Silicon: A New Material for MEMS," <i>Journal of Microelectromechanical Systems</i> 3(1):10-18, 1994
K.G	BS	Boswell, E.C. et al., "Polycrystalline Silicon Field Emitters," 8 th International Vacuum Microelectronics Conference Technical Digest, pp. 181-186, 1996

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FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 500466.03	APPLICATION NO. 10/789,479 not yet assigned
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Kie Y Ahn and Leonard Forbes	
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OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)					
K.G.	BT	Boswell, E.C. et al., "Polycrystalline silicon field emitters," <i>J Vac Sci Technol. B</i> 14(3):1910-1913, 1996			
	BU	Chalamala, Babu R. et al., "Fed Up with Fat Tubes," <i>IEEE Spectrum</i>, pp. 42-51, April 1998			
K.G.	BV	Huang, W.N. et al., "Photoluminescence in porous sputtered polysilicon films formed by chemical etching," <i>Semicond. Sci. Technol.</i> 12:228-233, 1997			
K.G.	BW	Huang, W.N. et al., "Properties of chemically etched porous polycrystalline silicon deposited by r.f. sputtering," <i>IEEE Hong Kong Electron Devices Meeting</i> , pp. 21-24, 1996			
K.G.	BX	Huq, S.E. et al., "Comparative study of gated single crystal silicon and polysilicon field emitters," <i>J. Vac. Sci. Technol. B</i> 15(6):2855-2858, 1997			
K.G.	BY	Huq, S.E. et al., "Fabrication of Gated Polycrystalline Silicon Field Emitters," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 367-370, 1996			
K.G.	BZ	Kim, I.H. et al., "Metal FEAs on Double Layer Structure of Polycrystalline Silicon," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 423-426, 1996			
K.G.	CA	Kim, I.H. et al., "Fabrication of metal field emitter arrays on polycrystalline silicon," <i>J. Vac. Sci. Technol. B</i> 15(2):468-471, 1997			
K.G.	CB	Ku, T.K. et al., "Enhanced Electron Emission from Phosphorus-Doped Diamond-Clad Silicon Field Emitter Arrays," <i>IEEE Electron Device Letters</i> 17(5):208-210, 1996			
K.G.	CC	Lacher, F. et al., "Electron field emission from thin fine-grained CVD diamond films," <i>Diamond and Related Materials</i> 6:1111-1116, 1997			
K.G.	CD	Lazarouk, S. et al., "Electrical characterization of visible emitting electroluminescent Schottky diodes based on n-type porous silicon and on highly doped n-type porous polysilicon," <i>Journal of Non-Crystalline Solids</i> 198-200:973-976, 1996			
K.G.	CE	Lee, J.H. et al., "A New Fabrication Method of Silicon Field Emitter Array with Local Oxidation of Polysilicon and Chemical-Mechanical-Polishing," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 415-418, 1996			
K.G.	CF	Lee, K.R. et al., "Field emission behavior of (nitrogen incorporated) diamond-like carbon films," <i>Thin Solid Films</i> 290-291:171-175, 1996			
K.G.	CG	Litovchenko, V.G. et al., "Emission Properties of the Silicon Cathodes Coated with Doped Diamond-Like Carbon Films," <i>IEEE International Conf. On Plasma Science</i> , p. 308, Abstract 7A02, 1997			
	CH	Nunes de Carvalho, C. et al., "Improvement of the Ito-P Interface in a Si:H Solar Cells Using a Thin SiO Intermediate Layer", <i>Mat. Res. Soc. Symp. Proc.</i> , 420:861-865, 1996			
K.G.	CI	Pullen, S.E. et al., "Enhanced Field Emission from Polysilicon Emitters Using Porous Silicon," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 211-214, 1996			
	CJ	Stevenson, I.C. et al., "Production of SiO₂ Films Over Large Substrate Area by Ion-Assisted Deposition of SiO with a Cold Cathode Source", <i>Soc. of Vac. Coaters, Proc. 36th Annual Tech. Conf.</i>, pp. 88-93, 1993			
K.G.	CK	Uh, H.S. et al., "Enhanced Electron Emission and Its Stability from Gated Mo-polycide Field Emitters," <i>IEEE</i> , pp. 713-716, 1997			
K.G.	CL	Uh, H.S. et al., "Fabrication and Characterization of Gated n+ Polycrystalline Silicon Field Emitter Arrays," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 419-422, 1996			
EXAMINER Karabi Guharay			DATE CONSIDERED 12/29/04		
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INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>		APPLICANT(S) Kie Y Ahn and Leonard Forbes	
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OTHER PRIOR ART <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
<u>KG</u>	CM	Uh, H.S., "Process design and emission properties of gated n+ polycrystalline silicon field emitter arrays for flat-panel display applications," <i>J. Vac. Sci. Technol. B</i> 15(2):472-476, 1997
<u>KG</u>	CN	Vaudaine, P. and Meyer, R., "Microtips Fluorescent Display," technical digest of IEDM 91, pp. 197-200, 1991
<u> </u>	CO	Zaidi, S.Z.A. et al., "Conduction Mechanisms in Co-Evaporated Mixed Mn/SiO _x Thin Films", <i>Journal of Materials Science</i> , 32:3349-3353, 1997
EXAMINER <u>Karabi Guharay</u>		DATE CONSIDERED <u>12/29/04</u>
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